



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

SOT-89 Plastic-Encapsulate Transistors

BF620 TRANSISTOR (NPN)

FEATURES

Power dissipation

P_{CM} : 500 mW ($T_{amb}=25^{\circ}C$)

Collector current

I_{CM} : 50 mA

Collector-base voltage

$V_{(BR)CBO}$: 300 V

Operating and storage junction temperature range

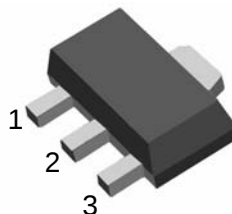
T_J, T_{stg} : $-55^{\circ}C$ to $+150^{\circ}C$

SOT-89

1. BASE

2. COLLECTOR

3. EMITTER



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}C$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=100\mu A, I_E=0$	300			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=1mA, I_B=0$	300			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=100\mu A, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=200V, I_E=0$			10	nA
Emitter cut-off current	I_{EBO}	$V_{EB}=5V, I_C=0$			50	nA
DC current gain	$h_{FE(1)}$	$V_{CE}=20V, I_C=25mA$	50			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=30mA, I_B=5mA$			0.6	V
Transition frequency	f_T	$V_{CE}=10V, I_C=100mA, f=100MHz$	60			MHz

Marking	DC
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